# 6<sup>th</sup> Generation CoolSiC<sup>™</sup>

### IDH04G65C6



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# 1 Maximum ratings

Table 3 Maximum ratings

Damana akan	Symbol	Values			11	A / 15.5
Parameter		Min.	Тур.	Max.	Unit	Note/Test condition
	$I_F$	_	_	4		$T_C \le 150 ^{\circ}\text{C}, D = 1$
Continuous forward current		-	_	7		$T_C \le 125 ^{\circ}\text{C}, D = 1$
		-	_	12		$T_c \le 25 ^{\circ}\text{C}, D = 1$
Surge-repetitive forward current, sine halfwave <sup>1</sup>	$I_{F,RM}$	-	-	18	A	$T_C = 25  ^{\circ}\text{C}, t_p = 10  \text{ms}$
Surge non-repetitive forward	,	_	_	29		$T_C = 25 ^{\circ}\text{C}, t_p = 10 \text{ms}$
current, sine halfwave	$I_{F,SM}$	_	_	23		$T_C = 150  ^{\circ}\text{C},  t_p = 10  \text{ms}$
Non-repetitive peak forward current	I <sub>F,max</sub>	-	-	250		$T_C = 25  ^{\circ}\text{C}, t_p = 10  \mu\text{s}$
:24	( :2 -1+	-	_	4.3	A2-	$T_C = 25 ^{\circ}\text{C}, t_\rho = 10 \text{ms}$
i <sup>2</sup> t value	∫ i²dt	_	_	2.7	A <sup>2</sup> s	$T_c = 150 ^{\circ}\text{C}, t_p = 10 \text{ms}$
Repetitive peak reverse voltage	$V_{RRM}$	_	_	650	٧	<i>T<sub>c</sub></i> = 25 °C
Diode dv/dt ruggedness	dv/dt	_	_	150	V/ns	V <sub>R</sub> = 0480 V
Power dissipation	P <sub>tot</sub>	_	_	45	W	$T_C = 25^{\circ}\text{C}, R_{thJC,max}$
Operating and storage temperature	$T_j$ $T_{stg}$	-55	-	175	°C	-
Mounting torque	_	_	_	70	Ncm	M3 screw

## 2 Thermal characteristics

Table 4 Thermal characteristics (PG-TO-220-2)

Davamatav	Complete		Values		l lm!t	Note/Test condition
Parameter	Symbol	Min.	Тур.	Max.	v. Unit	Note/Test condition
Thermal resistance, junction- case	$R_{thJC}$	-	2.0	3.4	12 /\AI	_
Thermal resistance, junctionambient	$R_{thJA}$	_	_	62	K/W	leaded
Soldering temperature, wavesoldering only allowed at leads	$T_{sold}$	-	-	260	°C	1.6 mm (0.063 in.) from case for 10 s

<sup>&</sup>lt;sup>1</sup> The surge-repetitive forward current test was performed with 1000 pulses (half-wave rectified sine with the 10 ms period).

Final Datasheet

3 Rev. 2.0, 2017-05-23



## 3 Electrical characteristics

### 3.1 Static characteristics

 Table 5
 Static characteristics

Davamatav	Complete		Values		Unit Note/Test condition		
Parameter	Symbol	Min.	Тур.	Max.	Unit	Note/Test condition	
DC blocking voltage	$V_{DC}$	650	_	_		<i>T<sub>j</sub></i> = 25 °C	
Diada famuard valtaga	17	_	1.25	1.35	V	$I_F = 4 \text{ A}, T_j = 25 ^{\circ}\text{C}$	
Diode forward voltage	$V_F$	_	1.5	_		,	
		_	0.4	14		$V_R = 420 \text{ V}, T_j = 25 \text{ °C}$	
Reverse current	$I_R$	_	13	_	μΑ	$V_R = 420 \text{ V}, T_j = 125 \text{ °C}$	
		_	31	_		$V_R = 420 \text{ V}, T_j = 150 \text{ °C}$	

#### 3.2 AC characteristics

Table 6 AC characteristics

Downwater	Cumbal		Values		Linit Noto/Tost Condition		
Parameter	Symbol	Min. Typ. Max.	Max.	Unit	Note/Test Condition		
Total capacitive charge	$Q_c$	-	6.9	-	nC	$V_R$ = 400 V, $T_j$ = 150 °C, di/dt = 200 A/µs, $I_F \le I_{F,MAX}$	
		-	205	-		$V_R = 1 \text{ V, } f = 1 \text{ MHz,}$ $T_j = 25 \text{ °C}$	
Total capacitance	С	_	12	-	pF	$V_R$ = 300 V, $f$ = 1 MHz, $T_j$ = 25 °C	
		_	12	$V_R = 600 \text{ V}, f = 1 \text{ MHz},$ $T_j = 25 \text{ °C}$	· · · · · · · · · · · · · · · · · · ·		



# 4 Diagrams

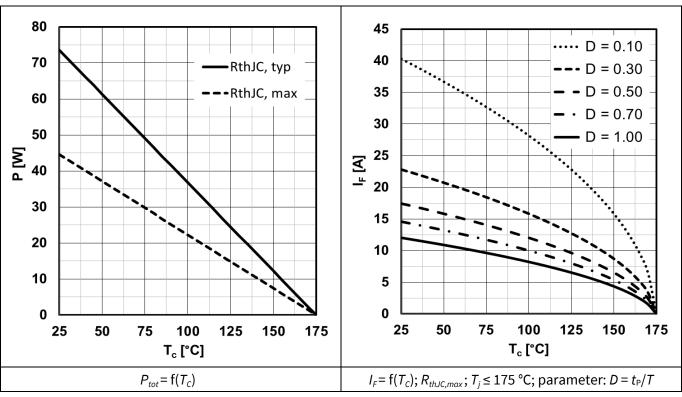


Figure 1 Power dissipation

Figure 2 Max. forward current

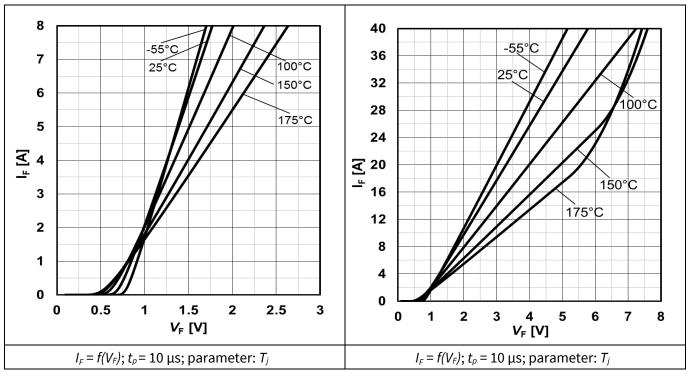


Figure 3 Typ. forward characteristics

Figure 4 Typ. forward characteristics in surge current



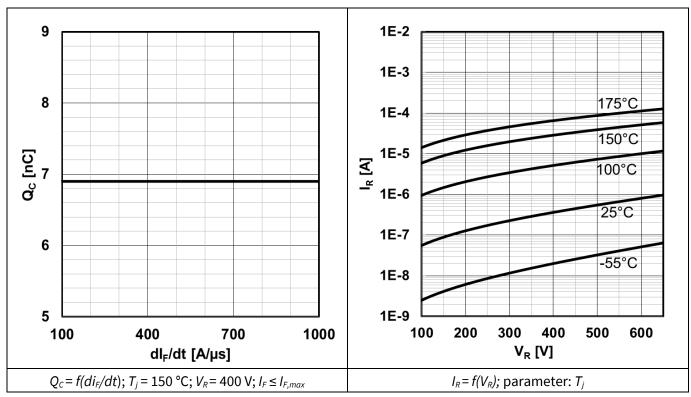
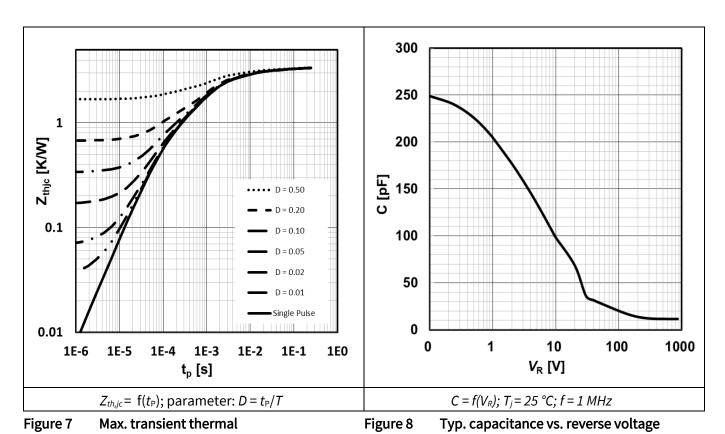


Figure 5 Typ. cap. charge vs. current slope Figure 6 Typ. reverse current vs. reverse voltage



impedance



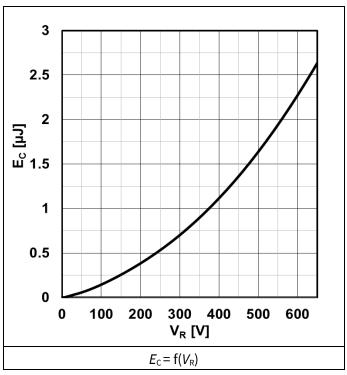


Figure 9 Typ. capacitance stored energy

# 5 Simplified forward characteristic

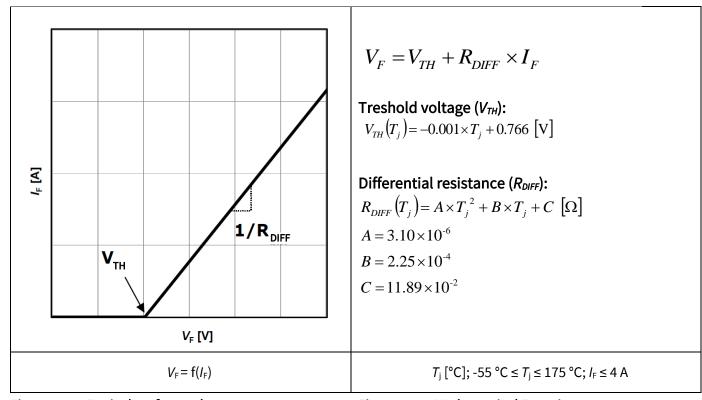


Figure 10 Equivalent forward current curve

Figure 11 Mathematical Equation



# 6 Package outlines

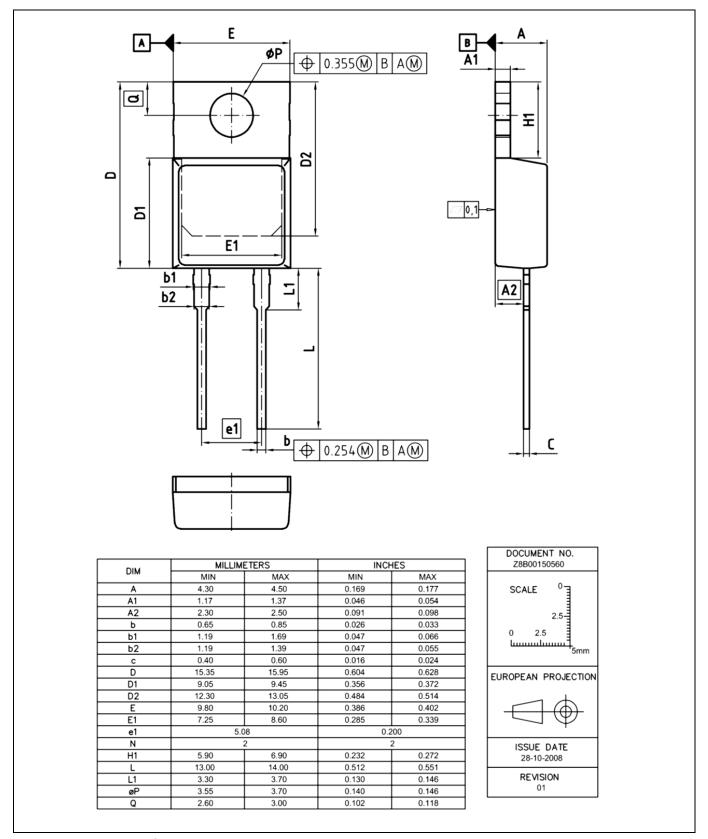


Figure 12 Outlines of the package PG-TO220-2, dimensions in mm/inches

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## **Revision History**

## Major changes since the last revision

Revision	Date	Subject (major changes since last revision)
2.0	2017-05-23	Release of final version

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